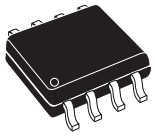
TSZ182H

Datasheet

Automotive-grade, very high accuracy (25 µV), high bandwidth (3 MHz), high temperature (150 °C), zero-drift operational amplifiers



SO8

Features

- AEC-Q100 qualified
- Very high accuracy and stability:
  - 25 µV max. offset voltage at 25 °C
  - 44 µV offset voltage over full temperature range
- Rail-to-rail input and output
- Low supply voltage: 2.2 - 5.5 V
- Low power consumption: 1 mA max. at 5 V
- Gain bandwidth product: 3 MHz
- Extended temperature range: -40 to 150 °C
- Micropackage: SO8
- Benefits:
  - Higher accuracy without calibration
  - Accuracy virtually unaffected by temperature change

Applications

- High accuracy signal conditioning
- Current measurement
- Sensor signal conditioning
- Automotive

Product status link
TSZ182H

Related products	
TSZ182	For -40/125 °C range

Description

The TSZ182H is a dual operational amplifier, featuring very low offset voltages with virtually zero-drift versus temperature changes. The TSZ182H offers rail-to-rail input and output, excellent speed/power consumption ratio, and 3 MHz gain bandwidth product, while consuming just 1 mA at 5 V. The device operates over an extended range of -40 to +150°C and features an ultra-low input bias current. These features make the TSZ182H ideal for high-accuracy high-bandwidth sensor interfaces for automotive environment.

1 Package pin connections

Figure 1. **Pin connections (top view)**

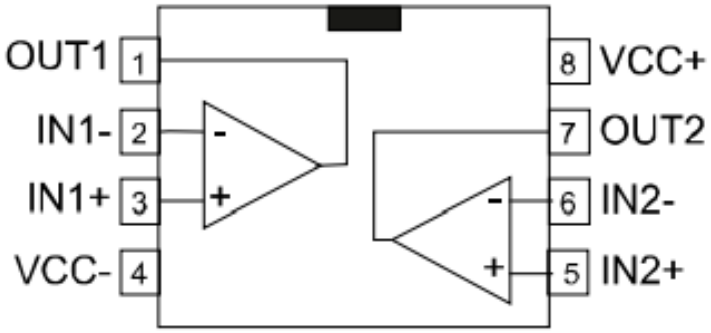


Table 1. **Pin description**

Pin	Pin name	Description
1	OUT1	Output
2	IN1 -	Negative input voltage
3	IN1 +	Positive input voltage
4	VCC -	Negative supply voltage
5	IN2 +	Positive input voltage
6	IN2 -	Negative input voltage
7	OUT2	Output
8	VCC +	Positive supply voltage

2 Absolute maximum ratings and operation conditions

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage (1)	6	V
V_{id}	Differential input voltage(2)	± V_{CC}	V
V_{in}	Input voltage(3)	(V_{CC}-)-0.2 to (V_{CC}+)+0.2	V
I_{in}	Input current(4)	10	mA
T_{stg}	Storage temperature	-65 to 150	°C
T_j	Junction temperature	160	°C
$R_{th\text{-}ja}$	Thermal resistance junction to ambient (5)(6) SO8	125	°C/W
ESD	Human body model (HBM)(7)	4	kV
	Charged device model (CDM)(8)	1.5	
	Latch-up immunity	200	mA

1. *All voltage values, except differential voltage, are with respect to network ground terminal.*
2. *The differential voltage is the non-inverting input terminal with respect to the inverting input terminal.*
3. *V_{CC} - V_{in} must not exceed 6 V, Vin must not exceed 6 V.*
4. *Input current must be limited by a resistor in series with the inputs.*
5. *R_{th} are typical values.*
6. *Short-circuits can cause excessive heating and destructive dissipation.*
7. *Human body model: 100 pF discharged through a 1.5 kΩ resistor between two pins of the device, done for all couples of pin combinations with other pins floating.*
8. *Charged device model: all pins plus packages are charged together to the specified voltage and then discharged directly to ground.*

Table 3. Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	2.2 to 5.5	V
V_{icm}	Common mode voltage on input pins	(V_{CC}-)-0.1 to (V_{CC}+)+0.1	V
T	Operating free-air temperature range	-40 to 150	°C

3 Electrical characteristics

Table 4. Electrical characteristics (V_{CC}+ = 2.2 V, V_{CC}- = 0 V, V_{icm} = V_{CC}/2, T = 25 °C, R_L=10 kΩ connected to V_{CC}/2, unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{IO}	Input offset voltage	T=25 °C		3.5	35	µV
		Tmin < T < Tmax			54	
$\|\Delta V_{IO}/\Delta T\|$	Input offset voltage drift(1)	Tmin < T < Tmax			0.15	µV/°C
I_{IB}	Input bias current(2)(V_{OUT}=V_{CC}/2)	T = 25 °C		30	200	pA
		Tmin < T < Tmax			400	
I_{IO}	Input offset current(2) (V_{OUT}=V_{CC}/2)	T = 25 °C		60	400	
		Tmin < T < Tmax			600	
CMR1	Common-mode rejection ratio(3), V_{ic} = 0 V to V_{CC}, V_{OUT} =V_{CC}/2, R_L>1 MΩ	T = 25 °C	96	115		dB
		Tmin < T < Tmax	90			
A_{vd}	Large signal voltage gain, V_{OUT} =0.5 V to (V_{CC} - 0.5 V)	T=25 °C	112	130		
		Tmin < T < Tmax	98			
V_{OH}	High-level output voltage, V_{OH} = V_{CC} - V_{OUT}	T=25 °C		15	40	mV
		Tmin < T < Tmax			70	
V_{OL}	Low-level output voltage	T = 25 °C		10	30	
		Tmin < T < Tmax			70	
I_{OUT}	I_{sink} (V_{OUT} = V_{CC})	T = 25 °C	4	6		mA
		Tmin < T < Tmax	2.37			
	I_{source} (V_{OUT} =0 V)	T = 25 °C	3.5	4		
		Tmin < T < Tmax	1.9			
I_{CC}	Supply current per channel, V_{OUT} = V_{CC}/2, R_L>1 MΩ	T = 25 °C		0.7	1	
		Tmin < T < Tmax			1.2	
AC performance						
GBP	Gain bandwidth product, R_L = 10 kΩ, C_L = 100 pF	T = 25 °C	1.6	2.3		MHz
		Tmin < T < Tmax	1.1			
Φ_m	Phase margin	R_L = 10 kΩ, C_L=100 pF		59		degrees
G_m	Gain margin			16		dB
S_R	Slew rate (4)	T=25 °C	3	4.6		V/µs
		Tmin < T < Tmax	2.5			
t_s	Settling time	To 0.1%, Vin = 0.8 Vpp		500		ns
en	Equivalent input noise voltage density	f = 1 kHz		50		nV/√Hz
		f =10 kHz		50		
en-pp	Voltage noise	f = 0.1 to 10 Hz		0.6		µVpp

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
C_s	Channel separation	f = 1 kHz		120		dB
t_{init}	Initialization time, G = 100[5]	T = 25 °C		60		µs
		Tmin < T < Tmax		100		

1. *Input offset measurements are performed on x100 gain configuration. The amplifiers and the gain setting resistors are at the same temperature.*
2. *Guaranteed by design.*
3. *CMR is defined as 20xLOG($\Delta_{Vicm}/\Delta_{Vio}$).*
4. *Slew rate value is calculated as the average between positive and negative slew rates.*
5. *Initialization time is defined as the delay between the moment when supply voltage exceeds 2.2 V and output voltage stabilization.*

Table 5. Electrical characteristics (V_{CC}+ = 3.3 V, V_{CC}- = 0 V, V_{icm} = V_{CC}/2, T = 25 °C, R_L=10 kΩ connected to V_{CC}/2, unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{IO}	Input offset voltage	T = 25 °C		2	30	µV
		Tmin < T < Tmax			49	
$\|\Delta V_{IO}/\Delta T\|$	Input offset voltage drift(1)	Tmin < T < Tmax			0.15	µV/°C
I_{IB}	Input bias current (V_{OUT}=V_{CC}/2)	T = 25 °C		30	200	pA
		Tmin < T < Tmax			400	
I_{IO}	Input offset current (2) (V_{OUT}=V_{CC}/2)	T = 25 °C		60	400	
		Tmin < T < Tmax			600	
CMR1	Common-mode rejection ratio (3), Vic=0 V to V_{CC}, V_{OUT} =V_{CC}/2, R_L>1 MΩ	T = 25 °C	104	120		dB
		Tmin < T < Tmax	100			
CMR2	Common-mode rejection ratio(3), V_{OUT} =V_{CC}/2, R_L>1 MΩ	T = 25 °C, V_{ic} = 0 to V_{CC}-1.8 V	106	132		
		Tmin < T < Tmax, V_{ic} = 0 to V_{CC}-2 V	104			
A_{vd}	Large signal voltage gain, V_{OUT} =0.5 V to (V_{CC} -0.5 V)	T = 25 °C	120	138		
		Tmin < T < Tmax	110			
V_{OH}	High-level output voltage, V_{OH} = V_{CC} - V_{OUT}	T = 25 °C		16	40	mV
		Tmin < T < Tmax			70	
V_{OL}	Low-level output voltage	T = 25 °C		11	30	
		Tmin < T < Tmax			70	
I_{OUT}	I_{sink} (V_{OUT} = V_{CC})	T = 25 °C	10	15		mA
		Tmin < T < Tmax	7.1			
	I_{source} (V_{OUT} =0 V)	T = 25 °C	6	11		
		Tmin < T < Tmax	3.8			
I_{CC}	Supply current per channel, V_{OUT} = V_{CC} /2, R_L>1 MΩ	T = 25 °C		0.7	1	
		Tmin < T < Tmax			1.2	
AC performance						
GBP	Gain bandwidth product, R_L=10 kΩ, C_L=100 pF	T = 25 °C	2	2.8		MHz
		Tmin < T < Tmax	1.5			
Φ_m	Phase margin	R_L = 10 kΩ, C_L = 100 pF		56		degrees
G_m	Gain margin			15		dB
SR	Slew rate(4)	T = 25 °C	2.6	4.5		V/µs
		Tmin < T < Tmax	2.1			
t_s	Settling time	To 0.1%, Vin = 1.2 Vpp		550		ns
e_n	Equivalent input noise voltage density	f=1 kHz		40		nV/√Hz
		f = 10 kHz		40		

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
en-pp	Voltage noise	f = 0.1 to 10 Hz		0.5		µVpp
C_s	Channel separation	f=1 kHz		120		dB
t_{int}	Initialization time, G=100 (5)	T = 25 °C		60		µs
		Tmin < T < Tmax		100		

1. *Input offset measurements are performed on x100 gain configuration. The amplifiers and the gain setting resistors are at the same temperature.*
2. *Guaranteed by design.*
3. *CMR is defined as 20xLOG($\Delta_{Vicm}/\Delta_{Vio}$).*
4. *Slew rate value is calculated as the average between positive and negative slew rates.*
5. *Initialization time is defined as the delay between the moment when supply voltage exceeds 2.2 V and output voltage stabilization.*

Table 6. Electrical characteristics (V_{CC}+ = 5 V, V_{CC}- = 0 V, V_{icm}=V_{CC}/2, T = 25 °C, R_L=10 kΩ connected to V_{CC}/2, unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{IO}	Input offset voltage	T = 25 °C		1	25	µV
		Tmin < T < Tmax			44	
$\|\Delta V_{IO}/\Delta T\|$	Input offset voltage drift(1)	Tmin < T < Tmax			0.15	µV/°C
I_{IB}	Input bias current (2) (V_{OUT}=V_{CC}/2)	T = 25 °C		30	200	pA
		Tmin < T < Tmax			400	
I_{IO}	Input offset current (2) (V_{OUT}=V_{CC}/2)	T = 25 °C		60	400	
		Tmin < T < Tmax			600	
CMR1	Common-mode rejection ratio(3), Vic=0 V to V_{CC}, V_{OUT} =V_{CC}/2, R_L>1 MΩ	T = 25 °C	108	126		dB
		Tmin < T < Tmax	106			
CMR2	Common-mode rejection ratio(3), V_{ic}=0 V to V_{CC} , V_{OUT} =V_{CC}/2, R_L>1 MΩ	T = 25 °C, V_{ic} = 0 to V_{CC}-1.8 V	112	136		
		Tmin < T < Tmax, Vic = 0 to V_{CC}-2 V	110			
SVR1	Supply voltage rejection ratio V_{CC}=2.2 to 5.5 V, V_{ic}=0 V, R_L>1 MΩ	T = 25 °C	105	123		
		Tmin < T < Tmax	104			
A_{vd}	Large signal voltage gain, V_{OUT} =0.5 V to (V_{CC} - 0.5 V)	T=25 °C	120	144		
		Tmin < T < Tmax	110			
EMIRR	EMI rejection ratio(5)	V_{RF}=100 mVp, f=400 MHz		52		
		V_{RF}=100 mVp, f=900 MHz		52		
		V_{RF}=100 mVp, f=1800 MHz		72		
		VRF=100 mVp, f=2400 MHz		85		
V_{OH}	High-level output voltage, V_{OH} = V_{CC} - V_{OUT}	T=25 °C		18	40	mV
		Tmin < T < Tmax			70	
V_{OL}	Low-level output voltage	T = 25 °C		13	30	
		Tmin < T < Tmax			70	
I_{OUT}	I_{sink} (V_{OUT} = V_{CC})	T = 25 °C	20	29		mA
		Tmin < T < Tmax	14			
	I_{source} (V_{OUT} =0 V)	T = 25 °C	15	25		
		Tmin < T < Tmax	9			
I_{CC}	Supply current per channel, V_{OUT} = V_{CC}/2, R_L>1 MΩ	T = 25 °C		0.8	1	
		Tmin < T < Tmax			1.2	
AC performance						
GBP	Gain bandwidth product, R_L=10 kΩ, C_L=100 pF	T=25 °C	2	3		MHz
		Tmin < T < Tmax	1.5			
Φ_m	Phase margin	R_L=10 kΩ, C_L=100 pF		56		Degrees
G_m	Gain margin			15		dB
SR	Slew rate(6)	T=25 °C	2.9	4.7		V/µs

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
SR	Slew rate(6)	Tmin < T < Tmax	2.4			V/µs
t_s	Settling time	To 0.1%, Vin=1.5 Vpp		600		ns
		To 0.01%, Vin=1 Vpp		4		µs
e_n	Equivalent input noise voltage density	f = 1 kHz		37		nV/√Hz
		f = 10 kHz		37		
en-pp	Voltage noise	f=0.1 to 10 Hz		0.4		µVpp
C_s	Channel separation	f = 100 Hz		135		dB
t_{init}	Initialization time, G=100(7)	T = 25 °C		60		µs
		Tmin < T < Tmax		100		

1. *Input offset measurements are performed on x100 gain configuration. The amplifiers and the gain setting resistors are at the same temperature.*
2. *Guaranteed by design*
3. *CMR is defined as 20xLOG($\Delta_{Vicm}/\Delta_{Vio}$).*
4. *SVR is defined as 20xLOG($\Delta Vcc/\Delta_{Vio}$).*
5. *EMIRR is defined as -20Log(VRF_Peak/Δ_{Vio}), tested on the MiniSO8 package, RF injection on the IN- pin.*
6. *Slew rate value is calculated as the average between positive and negative slew rates.*
7. *Initialization time is defined as the delay between the moment when supply voltage exceeds 2.2 V and output voltage stabilization.*

Figure 2. Supply current vs supply voltage

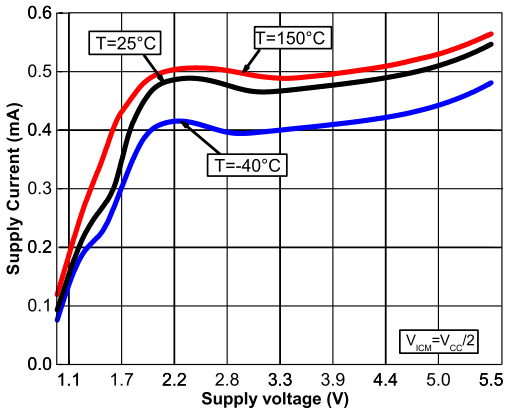


Figure 3. Input offset voltage distribution at V_{CC} = 5 V

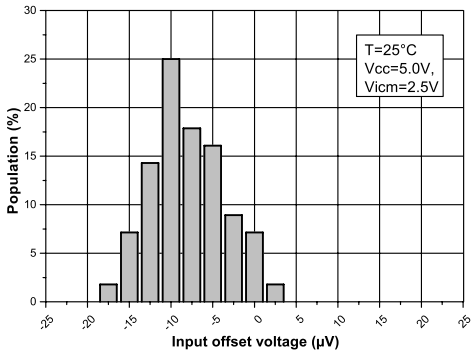


Figure 4. Input offset voltage distribution at V_{CC} = 3.3 V

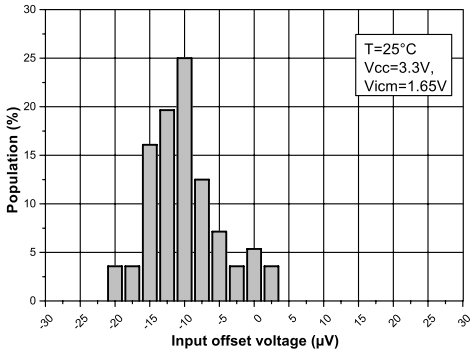


Figure 5. Input offset voltage distribution at V_{CC} = 2.2 V

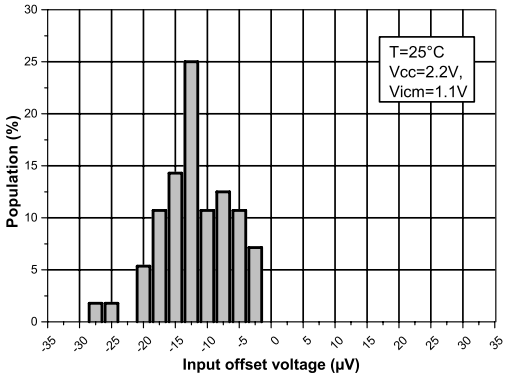


Figure 6. Input offset voltage distribution at V_{CC} = 5 V, T = 150 °C

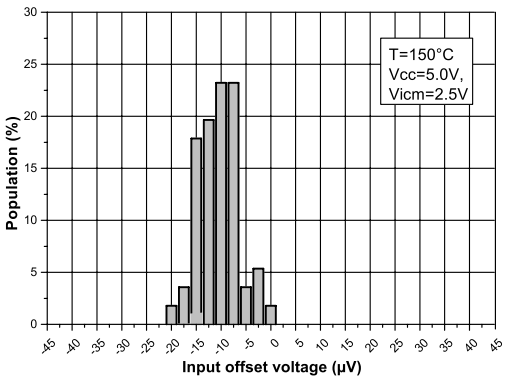


Figure 7. Input offset voltage distribution at V_{CC} = 5 V, T = -40 °C

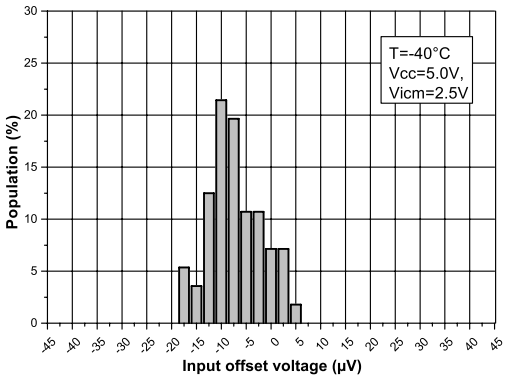


Figure 8. Input offset voltage distribution at V_{CC}=2.2 V, T = 150 °C

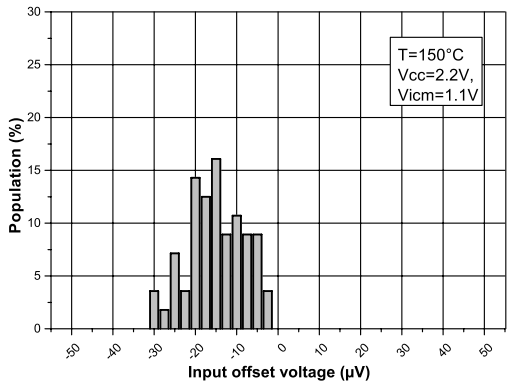


Figure 9. Input offset voltage distribution at V_{CC}=2.2 V, T = -40 °C

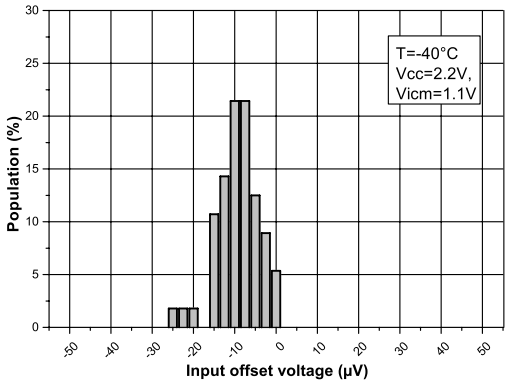


Figure 10. Input offset voltage vs supply voltage

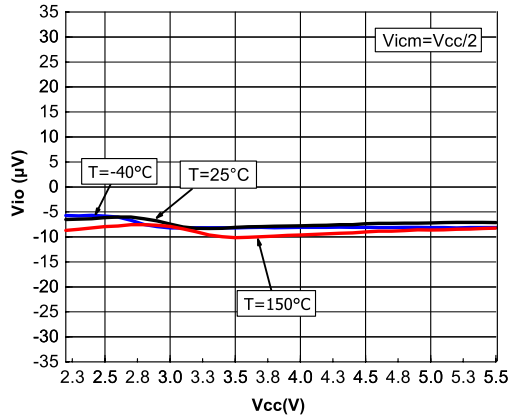


Figure 11. Input offset voltage vs input common mode at V_{CC}= 5 V

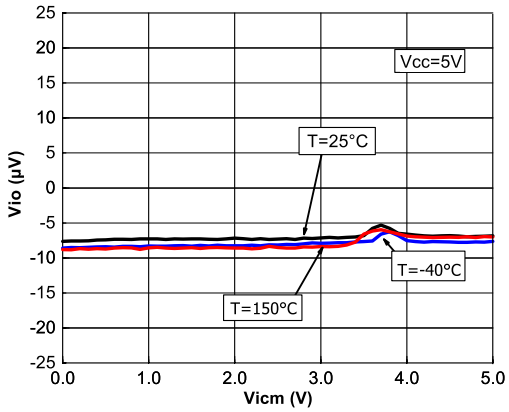


Figure 12. Input offset voltage vs input common mode at V_{CC}= 3.3 V

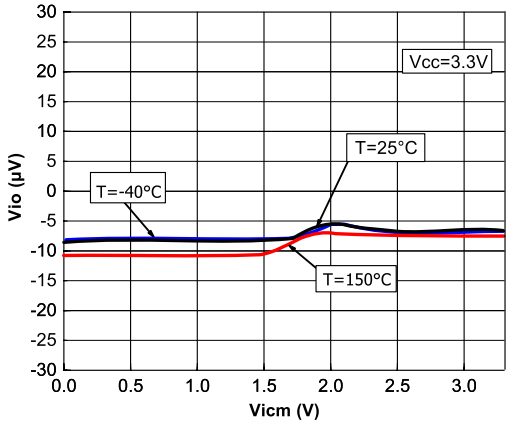


Figure 13. Input offset voltage vs input common mode at V_{CC}= 2.2 V

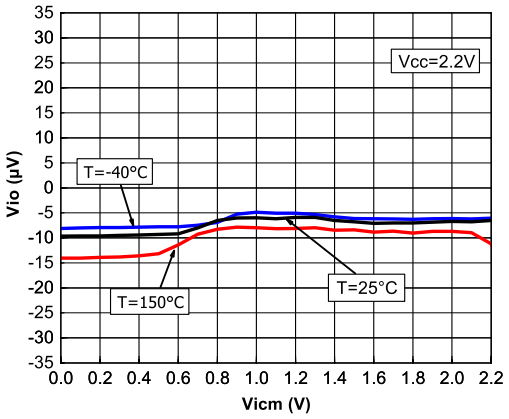


Figure 14. Input offset voltage vs temperature

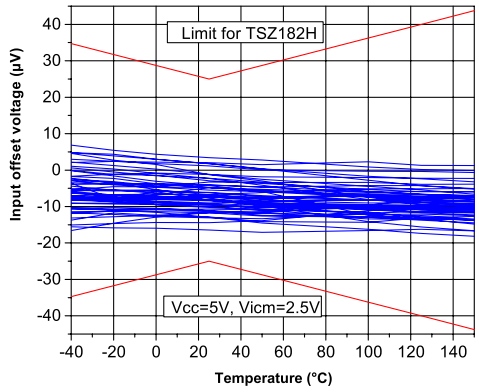


Figure 15. V_{OH} vs supply voltage

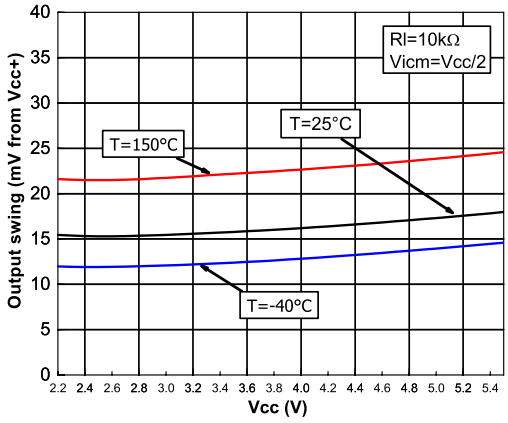


Figure 16. V_{OL} vs supply voltage

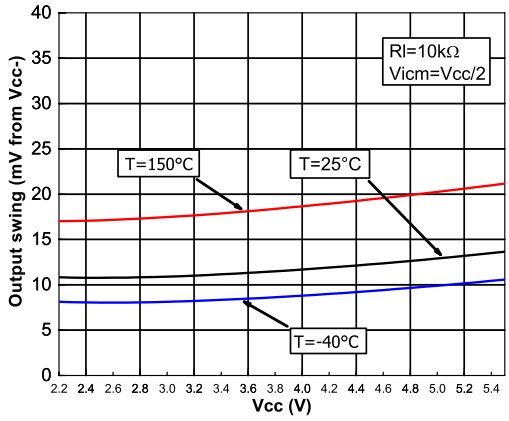


Figure 17. Output current vs output voltage at V_{CC} = 5 V

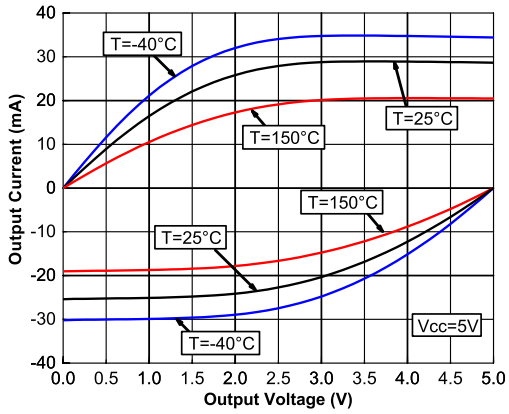


Figure 18. Output current vs. output voltage at V_{CC} = 2.2 V

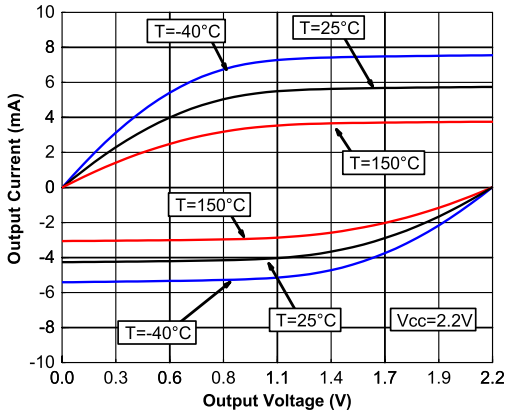


Figure 19. Input bias current vs common-mode at V_{CC} = 5 V

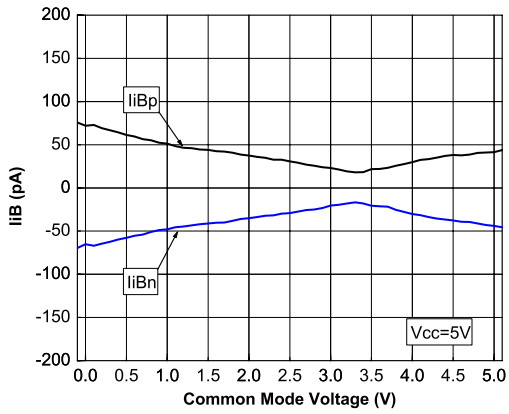


Figure 20. Input bias current vs. temperature at V_{CC} = 5 V

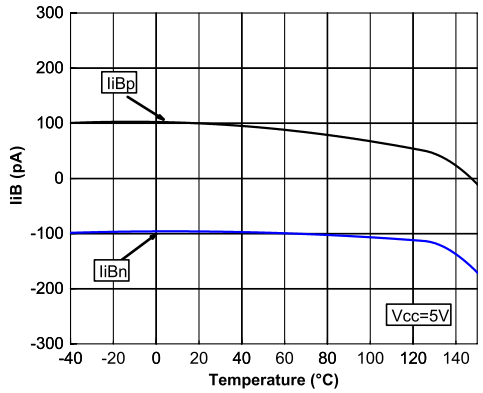


Figure 21. Output rail linearity

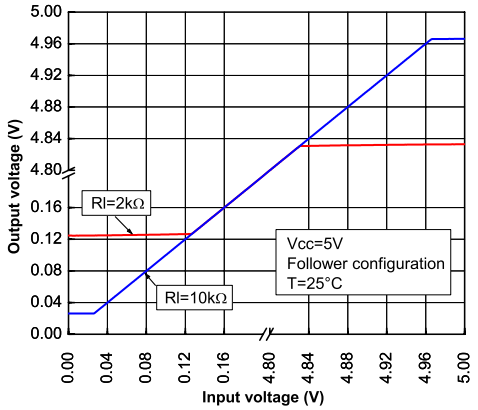


Figure 22. Bode diagram at V_{CC}=5 V

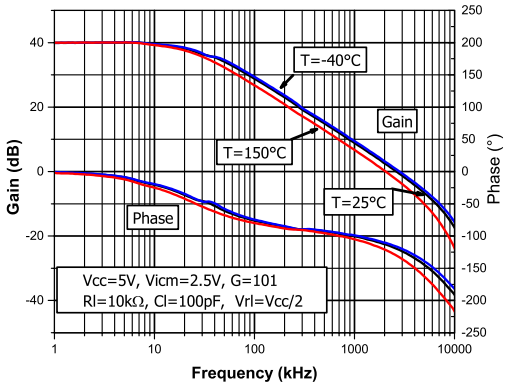


Figure 23. Bode diagram at V_{CC}=2.2 V

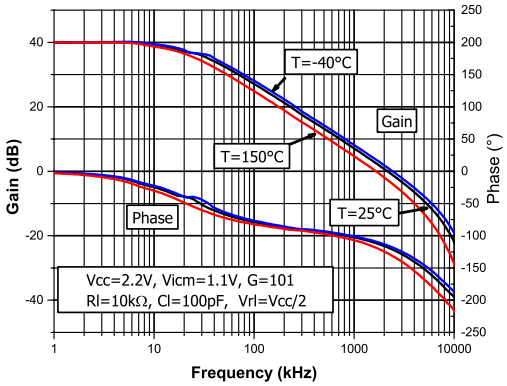


Figure 24. Bode diagram at V_{CC}=3.3 V

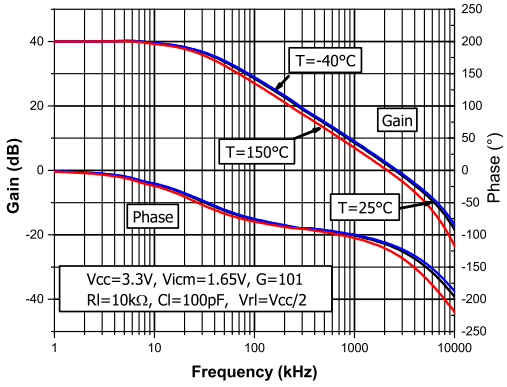


Figure 25. Open loop gain vs frequency

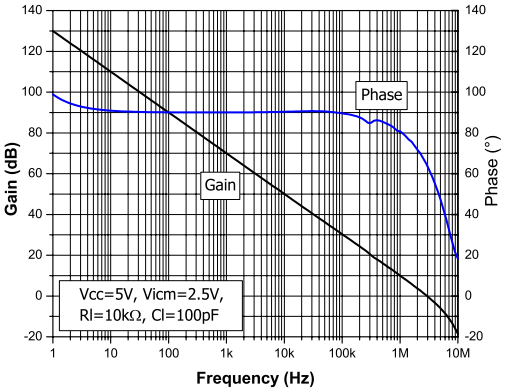


Figure 26. Positive slew rate vs supply voltage

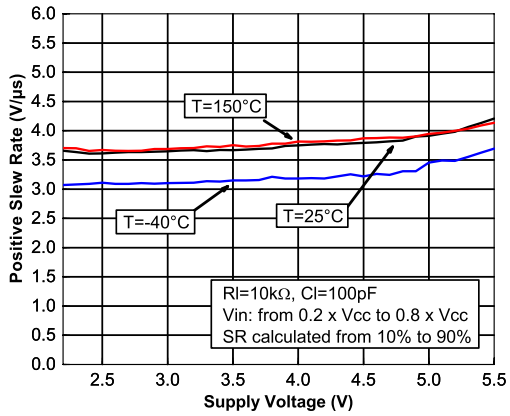


Figure 27. Negative slew rate vs supply voltage

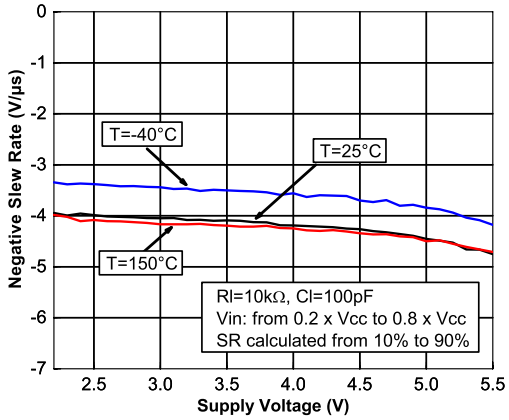


Figure 28. Noise 0.1 – 10 Hz vs time

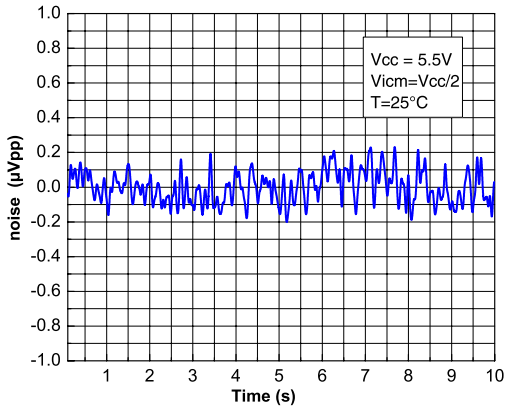


Figure 29. Noise vs frequency

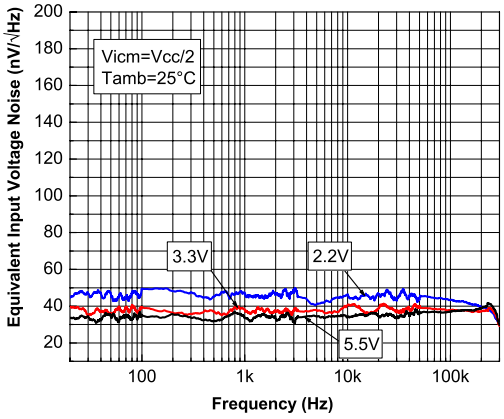


Figure 30. Output overshoot vs load capacitance

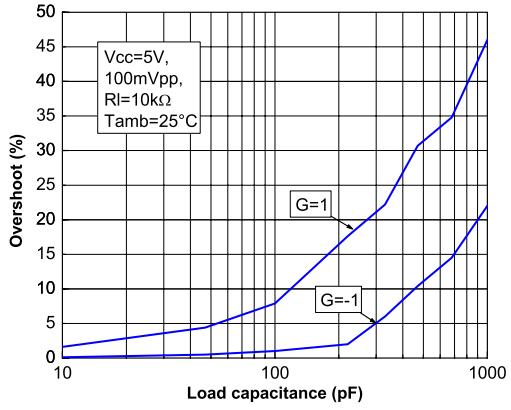


Figure 31. Small signal V_{CC} = 5 V

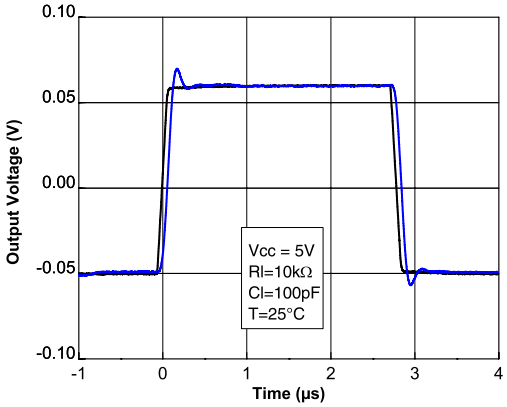


Figure 32. Small signal V_{CC} = 2.2 V

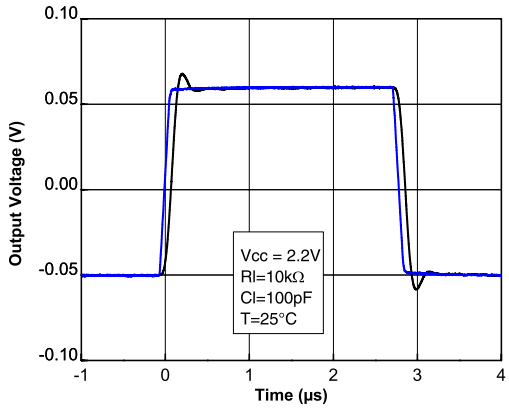


Figure 33. Large signal V_{CC} = 5 V

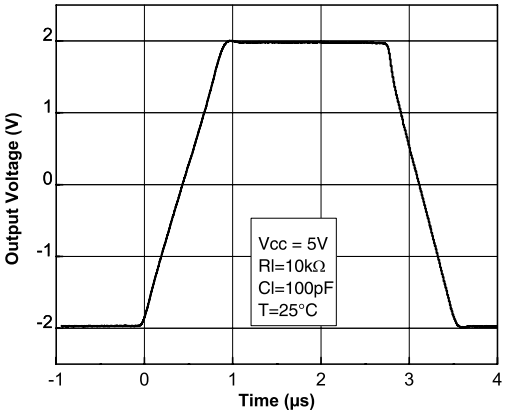


Figure 34. Large signal V_{CC} = 2.2 V

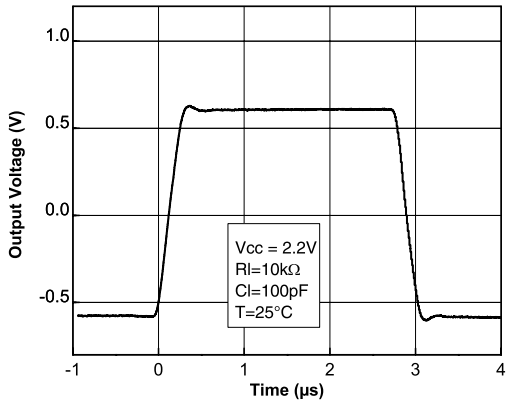


Figure 35. Negative overvoltage recovery V_{CC} = 2.2 V

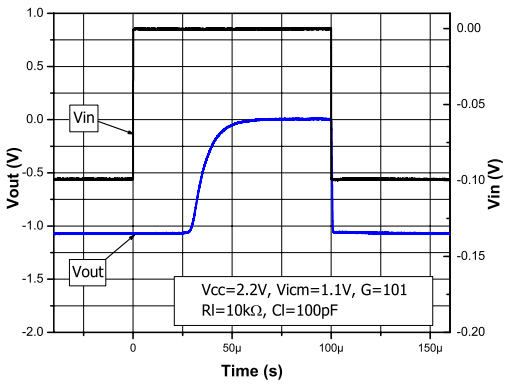


Figure 36. Positive overvoltage recovery V_{CC} = 5 V

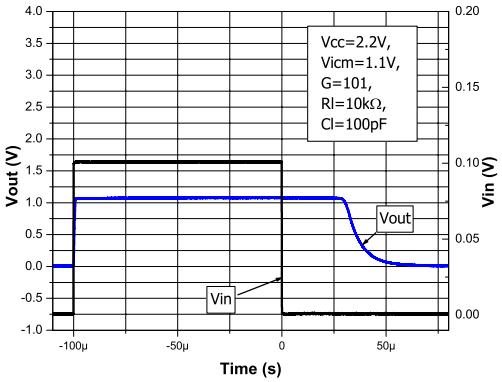


Figure 37. Output impedance vs frequency

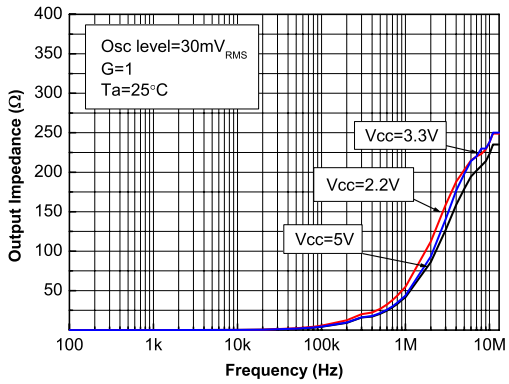


Figure 38. Settling time positive step (-2 V to 0 V)

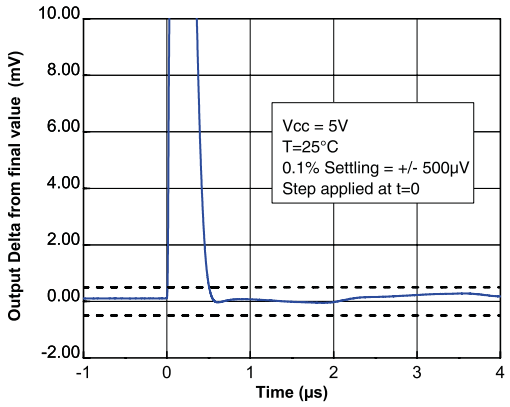


Figure 39. Settling time negative step (2 V to 0 V)

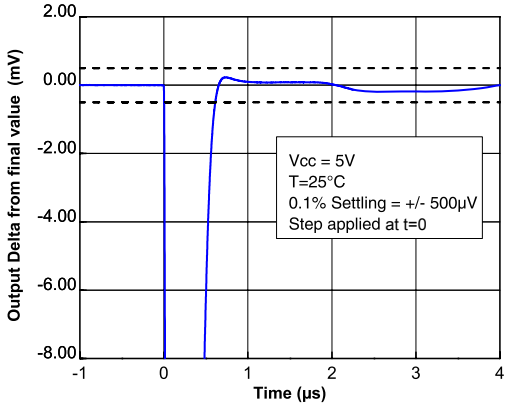


Figure 40. Settling time positive step (-0.8 V to 0 V)

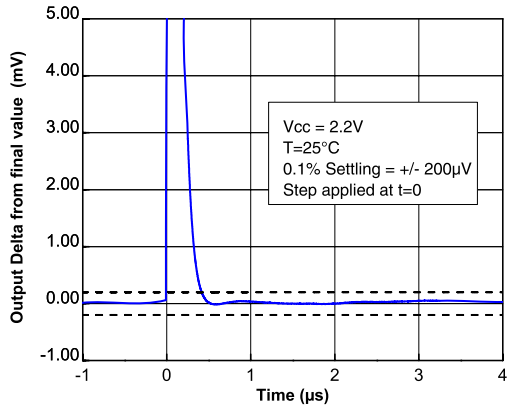


Figure 41. Settling time negative step (0.8 V to 0 V)

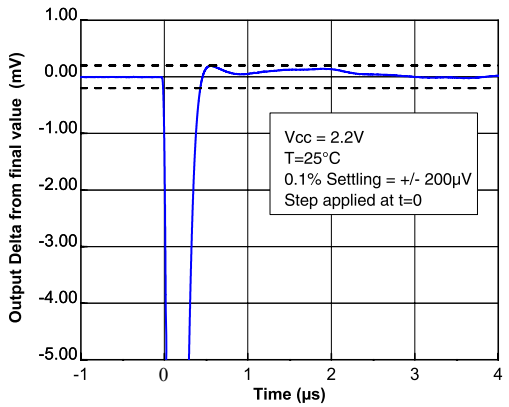


Figure 42. Maximum output voltage vs frequency

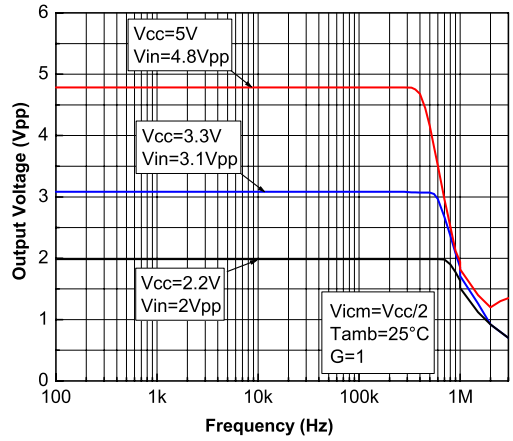


Figure 43. Crosstalk vs frequency

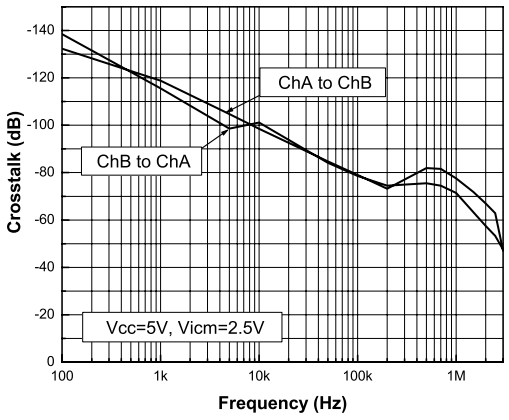
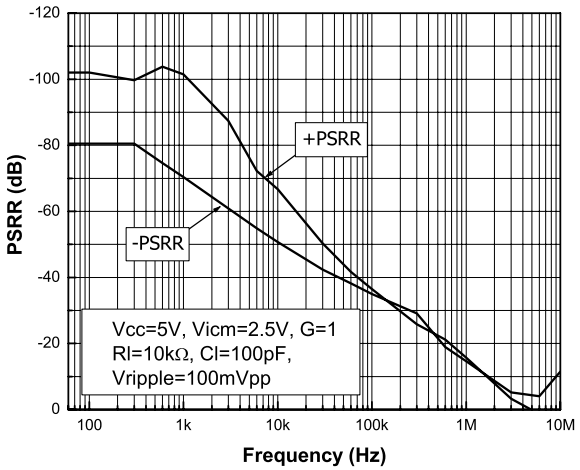


Figure 44. **PSSR vs frequency**



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 SO8 package information

Figure 45. SO8 package outline

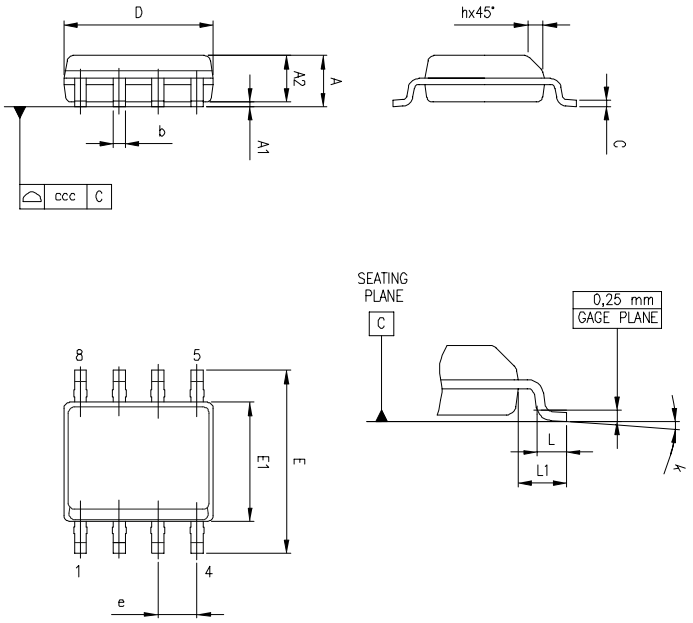


Table 7. SO-8 mechanical data

Dim.	mm			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
A1	0.1		0.25	0.004		0.01
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.01
D	4.8	4.9	5	0.189	0.193	0.197
E	5.8	6	6.2	0.228	0.236	0.244
E1	3.8	3.9	4	0.15	0.154	0.157
e		1.27			0.05	
h	0.25		0.5	0.01		0.02
L	0.4		1.27	0.016		0.05
L1		1.04			0.04	
k	0		8 °	1 °		8 °
ccc			0.1			0.004

5 Ordering information

Table 8. **Ordering information**

Order code	Package	Packing	Marking
TSZ182HYDT	SO8	Tape and reel	TSZ182H

Revision history

Table 9. **Document revision history**

Date	Version	Changes
20-Jan-2020	1	Initial release.

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